

Ultralow Power, Rail-to-Rail Output Operational Amplifiers

OP281/OP481

FEATURES

Low Supply Current: 4 µA/Amplifier Max Single-Supply Operation: 2.7 V to 12 V Wide Input Voltage Range Rail-to-Rail Output Swing Low Offset Voltage: 1.5 mV No Phase Reversal

APPLICATIONS

Comparator Battery-Powered Instrumentation Safety Monitoring Remote Sensors Low Voltage Strain Gage Amplifiers

GENERAL DESCRIPTION

The OP281 and OP481 are dual and quad ultralow power, singlesupply amplifiers featuring rail-to-rail outputs. Each operates from supplies as low as 2.0 V and are specified at +3 V and +5 V single supply as well as ± 5 V dual supplies.

Fabricated on Analog Devices' CBCMOS process, the OP281/OP481 features a precision bipolar input and an output that swings to within millivolts of the supplies and continues to sink or source current all the way to the supplies.

Applications for these amplifiers include safety monitoring, portable equipment, battery and power supply control, and signal conditioning and interfacing for transducers in very low power systems.

The output's ability to swing rail-to-rail and not increase supply current, when the output is driven to a supply voltage, enables the OP281/OP481 to be used as comparators in very low power systems. This is enhanced by their fast saturation recovery time. Propagation delays are 250 µs.

The OP281/OP481 are specified over the extended industrial temperature range (-40°C to +85°C). The OP281 dual amplifier is available in 8-lead SOIC surface-mount and TSSOP packages. The OP481 quad amplifier is available in narrow 14-lead SOIC and TSSOP packages.

PIN CONFIGURATIONS

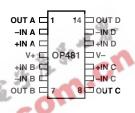
8-Lead SOIC (R Suffix)

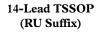
	1 8	⊐ v+
–IN A 🗖	OP281	🗅 ООТ В
+IN A 🗖	0F201	🗆 –IN В
v– ⊏	45	⊐ +IN B

8-Lead TSSOP (RU Suffix)



14-Lead Narrow-Body SOIC (R Suffix)





OP481

NOTE: PIN ORIENTATION IS EQUIVALENT FOR EACH PACKAGE VARIATION

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OP281/OP481-SPECIFICATIONS

ELECTRICAL SPECIFICATIONS (@ $V_s = 3.0 V$, $V_{CM} = 1.5 V$, $T_A = 25^{\circ}C$, unless otherwise noted.*)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	Vos	Note 1			1.5	mV
		$-40^{\circ}C \le T_A \le +85^{\circ}C$			2.5	mV
Input Bias Current	I _B	$-40^{\circ}C \le T_{A} \le +85^{\circ}C$		3	10	nA
Input Offset Current	I _{OS}	$-40^{\circ}C \le T_A \le +85^{\circ}C$		0.1	7	nA
Input Voltage Range	-03		0		2	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 0 V$ to 2.0 V,	-			
		$-40^{\circ}C \le T_A \le +85^{\circ}C$	65	95		dB
Large Signal Voltage Gain	A _{VO}	$R_{\rm L} = 1 M\Omega, V_{\rm O} = 0.3 V \text{ to } 2.7 V$	5	13		V/mV
		$-40^{\circ}C \le T_{A} \le +85^{\circ}C$	2			V/mV
Offset Voltage Drift	$\Delta V_{OS}/DT$		_	10		μV/°C
Bias Current Drift	$\Delta I_{\rm B}/{\rm DT}$			20		pA/°C
Offset Current Drift	$\Delta I_{OS}/DT$			2		pA/°C
				-		P11 0
OUTPUT CHARACTERISTICS						
Output Voltage High	V _{OH}	$R_{\rm L} = 100 \rm k\Omega$ to GND,				
		$-40^{\circ}C \le T_A \le +85^{\circ}C$	2.925	2.96		V
Output Voltage Low	V _{OL}	$R_L = 100 \text{ k}\Omega$ to V+,				
		$-40^{\circ}C \le T_A \le +85^{\circ}C$		25	75	mV
Short Circuit Limit	I _{SC}		-	± 1.1		mA
POWER SUPPLY		$V_{S} = 2.7 V \text{ to } 12 V,$ -40°C ≤ $T_{A} \le +85^{\circ}C$ $V_{O} = 0 V$ -40°C ≤ $T_{A} \le +85^{\circ}C$	10-1-			
Power Supply Rejection Ratio	PSRR	$V_{\rm S} = 2.7 \text{ V}$ to 12 V,				
		$-40^{\circ}C \le T_{A} \le +85^{\circ}G_{A}$	76	95		dB
Supply Current/Amplifier	I _{SY}	$V_0 = 0 V$		3	4	μA
		$-40^{\circ}C \le T_A \le +85^{\circ}C$			5	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_{L} = 100 \text{ k}\Omega, C_{L} = 50 \text{ pF}$		25		V/ms
Turn On Time	SK	$A_V = 1, V_O = 1$		23 40		
Turn On Time		$A_{\rm V} = 1, {\rm v}_{\rm O} = 1$ $A_{\rm V} = 20, {\rm v}_{\rm O} = 1$		40 50		μs
		$A_{\rm V} = 20, \ {\rm v}_{\rm O} = 1$		50 65		μs
Saturation Recovery Time	GBP					μs 1-TT-
Gain Bandwidth Product				95 70		kHz
Phase Margin	φο			70		Degrees
NOISE PERFORMANCE						
Voltage Noise	e _n p-p	0.1 Hz to 10 Hz		10		μV p-p
Voltage Noise Density	e _n	f = 1 kHz		75		nV/\sqrt{Hz}
Current Noise Density	in			<1		pA/√Hz

 $^{*}V_{OS}$ is tested under a no load condition.

Specifications subject to change without notice.

OP281/0P481

ELECTRICAL SPECIFICATIONS (@ $V_s = 5.0 \text{ V}$, $V_{CM} = 2.5 \text{ V}$, $T_A = 25^{\circ}\text{C}$, unless otherwise noted.*)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	Vos	Note 1		0.1	1.5	mV
		$-40^{\circ}C \le T_A \le +85^{\circ}C$			2.5	mV
Input Bias Current	IB	$-40^{\circ}C \le T_A \le +85^{\circ}C$		3	10	nA
Input Offset Current	I _{OS}	$-40^{\circ}C \le T_A \le +85^{\circ}C$		0.1	7	nA
Input Voltage Range			0		4	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 0 V$ to 4.0 V,				
		$-40^{\circ}C \le T_A \le +85^{\circ}C$	65	90		dB
Large Signal Voltage Gain	A _{VO}	$R_L = 1 M\Omega$, $V_O = 0.5 V$ to 4.5 V	5	15		V/mV
		$-40^{\circ}C \le T_A \le +85^{\circ}C$	2			V/mV
Offset Voltage Drift	$\Delta V_{OS}/DT$	-40° C to $+85^{\circ}$ C		10		μV/°C
Bias Current Drift	$\Delta I_{\rm B}/{\rm DT}$			20		pA/°C
Offset Current Drift	$\Delta I_{OS}/DT$			2		pA/°C
OUTPUT CHARACTERISTICS						
Output Voltage High	V _{OH}	$R_{\rm L} = 100 \text{ k}\Omega$ to GND,				
		$-40^{\circ}C \le T_A \le +85^{\circ}C$	4.925	4.96		V
Output Voltage Low	V _{OL}	$R_{\rm L} = 100 \rm k\Omega$ to V+,				
		$-40^{\circ}C \le T_A \le +85^{\circ}C$		25	75	mV
Short Circuit Limit	I _{SC}		-	±3.5		mA
POWER SUPPLY		$V_{S} = 2.7 V \text{ to } 12 V,$ -40°C ≤ $T_{A} \le +85^{\circ}C$ $V_{O} = 0 V$				
Power Supply Rejection Ratio	PSRR	$V_{\rm S} = 2.7 \text{ V}$ to 12 V,				
		$V_{\rm S} = 2.7 \text{ V to } 12 \text{ V},$ $-40^{\circ}\text{C} \leq T_{\rm A} \leq +85^{\circ}\text{C}$	76	95		dB
Supply Current/Amplifier	I _{SY}	$V_0 = 0 V$		3.2	4	μA
	01	$-40^{\circ}C \le T_A \le +85^{\circ}C$			5	μΑ
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_{\rm L} = 100 \text{ k}\Omega, C_{\rm L} = 50 \text{ pF}$		27		V/ms
Saturation Recovery Time				120		μs
Gain Bandwidth Product	GBP			100		kHz
Phase Margin	фо			74		Degree
NOISE PERFORMANCE						
Voltage Noise	e _n p-p	0.1 Hz to 10 Hz		10		μV p-p
Voltage Noise Density	e _n	f = 1 kHz		75		nV/\sqrt{H}
Current Noise Density	in			<1		pA/√H

 $^{\ast}V_{OS}$ is tested under a no load condition.

Specifications subject to change without notice.

ELECTRICAL SPECIFICATIONS (@ $V_s = \pm 5.0 V$, $T_A = +25^{\circ}C$, unless otherwise noted.*)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	Vos	Note 1		0.1	1.5	mV
		$-40^{\circ}C \le T_A \le +85^{\circ}C$			2.5	mV
Input Bias Current	I _B	$-40^{\circ}C \le T_A \le +85^{\circ}C$		3	10	nA
Input Offset Current	I _{OS}	$-40^{\circ}C \le T_A \le +85^{\circ}C$		0.1	7	nA
Input Voltage Range			-5		+4	V
Common-Mode Rejection	CMRR	$V_{CM} = -5.0 \text{ V to } +4.0 \text{ V},$				
		$-40^{\circ}C \le T_A \le +85^{\circ}C$	65	95		dB
Large Signal Voltage Gain	A _{VO}	$R_{\rm L} = 1 \ M\Omega, V_{\rm O} = \pm 4.0 \ V,$	5	13		V/mV
		$-40^{\circ}C \le T_A \le +85^{\circ}C$	2			V/mV
Offset Voltage Drift	$\Delta V_{OS}/DT$	-40°C to +85°C		10		µV/°C
Bias Current Drift	$\Delta I_{B}/DT$			20		pA/°C
Offset Current Drift	$\Delta I_{OS}/DT$			2		pA/°C
OUTPUT CHARACTERISTICS						
Output Voltage Swing	Vo	$R_{\rm L} = 100 \ \rm k\Omega$ to GND,				
r a g a g		$-40^{\circ}C \le T_A \le +85^{\circ}C$	±4.925	± 4.98		V
Short Circuit Limit	I _{SC}			12		mA
POWER SUPPLY						
	PSRR	$V_{\rm S} = \pm 1.35 {\rm V}$ to $\pm 6 {\rm V}$,	- 10			
TF 5), the second s	-	$-40^{\circ}C \le T_{A} \le +85^{\circ}C$	76	95		dB
Supply Current/Amplifier	I _{SY}	$V_0 = 0 V$	2.2	3.3	5	μA
Input Offset Current Input Voltage Range Common-Mode Rejection Large Signal Voltage Gain Offset Voltage Drift Bias Current Drift Offset Current Drift UTPUT CHARACTERISTICS Output Voltage Swing Short Circuit Limit OWER SUPPLY Power Supply Rejection Ratio Supply Current/Amplifier OYNAMIC PERFORMANCE Slew Rate Gain Bandwidth Product Phase Margin IOISE PERFORMANCE Voltage Noise Voltage Noise Voltage Noise Density Voltage Noise Density	51	$V_{S} = \pm 1.35 \text{ V to } \pm 6 \text{ V},$ -40°C ≤ T _A ≤ +85°C $V_{O} = 0 \text{ V}$ -40°C ≤ T _A ≤ +85°C $R_{L} = 100 \text{ k}\Omega, C_{L} = 50 \text{ pF}$			6	μA
DYNAMIC PERFORMANCE						
	±SR	$R_{\rm r} = 100 \ k\Omega, C_{\rm r} = 50 \ pF$		28		V/ms
	GBP			105		kHz
Phase Margin	φο			75		Degrees
	e n-n	0.1 Hz to 10 Hz		10		μV p-p
	e _n p-p e _n	f = 1 kHz		85		nV/\sqrt{Hz}
	e _n	f = 10 kHz		75		nV/\sqrt{Hz}
Current Noise Density	i _n			<1		pA/\sqrt{Hz}
*V _{OS} is tested under a no load condition.	*n			1		PIN 11Z

 $^{*}V_{OS}$ is tested under a no load condition.

Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS*

Supply Voltage 16 V
Input Voltage GND to V_{S} + 10 V
Differential Input Voltage ±3.5 V
Output Short-Circuit Duration to GND Indefinite
Storage Temperature Range65°C to +150°C
Operating Temperature Range40°C to +85°C
Junction Temperature Range65°C to +150°C
Lead Temperature Range (Soldering, 60 sec) 300°C

*Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposures to absolute maximum rating conditions for extended periods may affect device reliability.

Package Type	θ_{JA}^*	θ _{JC}	Unit
8-Lead SOIC (R)(S)	158	43	°C/W
8-Lead TSSOP (RU)	240	43	°C/W
14-Lead SOIC (R)(S)	120	36	°C/W
14-Lead TSSOP (RU)	240	43	°C/W

 θ_{IA} is specified for the worst-case conditions, i.e., θ_{IA} is specified for device soldered in circuit board for TSSOP and SOIC packages.

CAUTION _

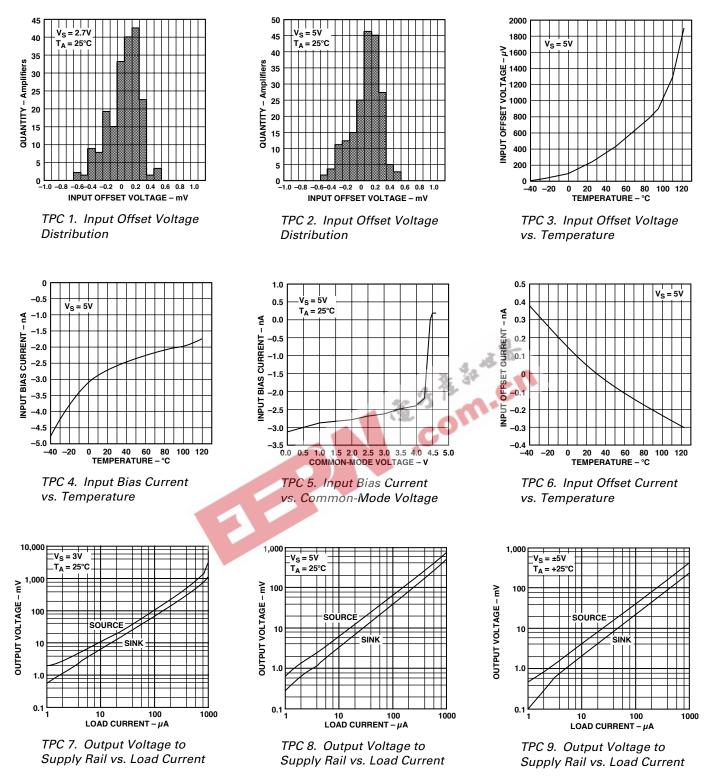
A Sand R ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the OP281/OP481 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

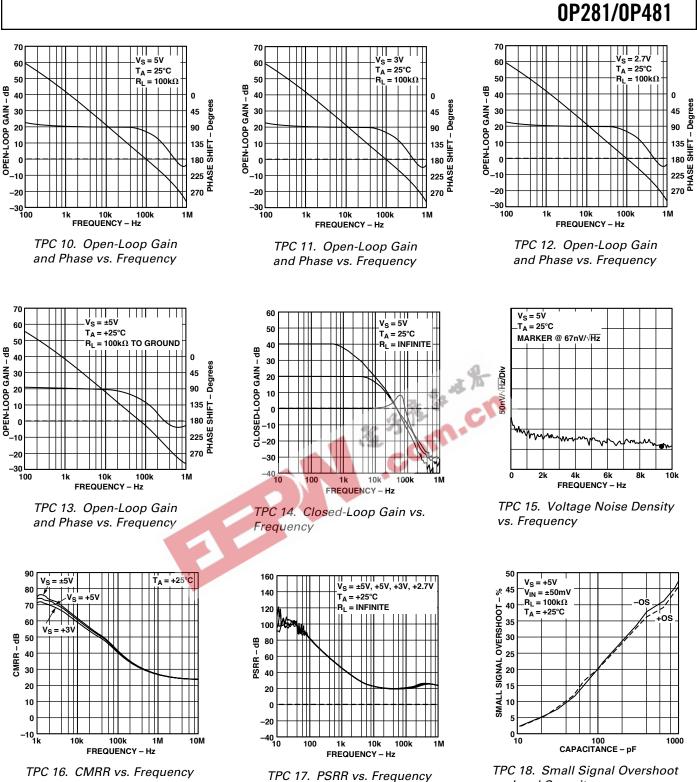


ORDERING GUIDE

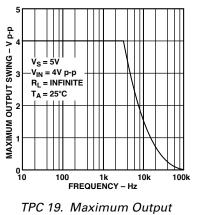
Model	Temperature	Package	Package
	Range	Description	Option
OP281GS	-40°C to +85°C	8-Lead SOIC	R-8
OP281GRU	-40°C to +85°C	8-Lead TSSOP	RU-8
OP481GS	-40°C to +85°C	14-Lead SOIC	R-14
OP481GRU	-40°C to +85°C	14-Lead TSSOP	RU-14

OP281/OP481–Typical Performance Characteristics

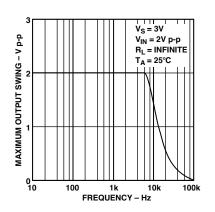




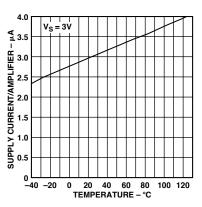
TPC 18. Small Signal Overshoot vs. Load Capacitance



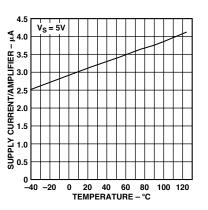
Swing vs. Frequency



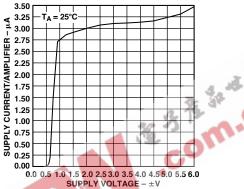
TPC 20. Maximum Output Swing vs. Frequency

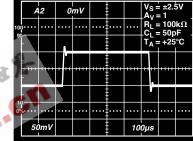


TPC 21. Supply Current/Amplifier vs. Temperature



TPC 22. Supply Current/Amplifier vs. Temperature





TPC 23. Supply Current/Amplifier vs. Supply Voltage

TPC 24. Small Signal Transient Response

	A2		A2 0mV		mV			V _S = ±1.35V A _V = 1 R _L = 100kΩ					
10				•••	••••	•••••		••••	RL	= 100	kΩ		
90									CL: TA	= 50p = +25	F - ℃		
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	-		ľ										
									۳ŕ-				
1													
09	‰••••	••••	•••	•••	••••	••••		••••	••••	••••			
	50mV							10	0µs				

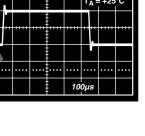
TPC 25. Small Signal Transient Response

	2	2.:	50V				V _S =	= 5V = 1 = 100	
100	••••	••••			••••		RL = CL = TA =	kΩ F.	
							TA	C	
-		.,/					λ		
		/					Ļ		
10	_/								
0%•••••	••••	••••	••••	•••••	•••••	•••••	••••	••••	••••
1	V					10	0µs		

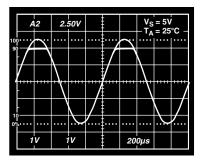
TPC 26. Large Signal Transient Response

A	A2		50V				iV		
100	••••		••••				Ri =	= 100	kΩ
		\square					C _L = 50pF T _A = 25°C		
		/			İ				
	· · ·)								
-	_/						L		
0%****	••••	••••	••••			••••	••••	••••	••••
5	00m	v				10	0µs		

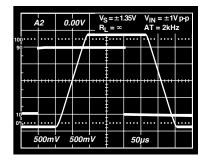
TPC 27. Large Signal Transient Response



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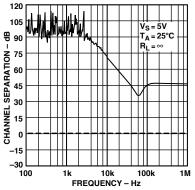
TPC 28. No Phase Reversal



TPC 29. Saturation Recovery Time

A	2	0.0	oov			CI		T = A	VOL 2.5V
100 • • • • • 90	••••	••••	••/					s = ± a = +2 i = ∞	25°C
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0%			•••••	•••••	•••••	•••••	•••••		
1	V	5	00m	V		10	0µs		

TPC 30. Saturation Recovery Time



TPC 31. Channel Separation vs. Frequency

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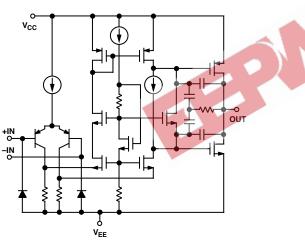
OP281/0P481

APPLICATIONS

Theory of Operation

The OPx81 family of op amps is comprised of extremely low powered, rail-to-rail output amplifiers, requiring less than $4 \mu A$ of quiescent current per amplifier. Many other competitors' devices may be advertised as low supply current amplifiers but draw significantly more current as the outputs of these devices are driven to a supply rail. The OPx81's supply current remains under $4 \mu A$ even with the output driven to either supply rail. Supply currents should meet the specification as long as the inputs and outputs remain within the range of the power supplies.

Figure 1 shows a simplified schematic of a single channel for the OPx81. A bipolar differential pair is used in the input stage. PNP transistors are used to allow the input stage to remain linear with the common-mode range extending to ground. This is an important consideration for single-supply applications. The bipolar front end also contributes less noise than a MOS front end with only nano-amps of bias currents. The output of the op amp consists of a pair of CMOS transistors in a common source configuration. This setup allows the output of the amplifier to swing to within millivolts of either supply rail. The headroom required by the output stage is limited by the amount of current being driven into the load. The lower the output current, the closer the output voltage headroom versus load current. This behavior is typical of rail-to-rail output amplifiers.





Input Overvoltage Protection

The input stage to the OPx81 family of op amps consists of a PNP differential pair. If the base voltage of either of these input transistors drops to more than 0.6 V below the negative supply, the input ESD protection diodes will become forward biased, and large currents will begin to flow. In addition to possibly damaging the device, this will create a phase reversal effect at the output. To prevent these effects from happening, the input current should be limited to less than 0.5 mA.

This can be done quite easily by placing a resistor in series with the input to the device. The size of the resistor should be proportional to the lowest possible input signal excursion and can be found using the following formula:

$$R = \frac{V_{EE} - V_{IN, MIN}}{0.5 \times 10^{-3}}$$

where:

 V_{EE} is the negative power supply for the amplifier. $V_{IN, MIN}$ is the lowest input voltage excursion expected.

For example, a single channel of the OPx81 is to be used with a single-supply voltage of +5 V where the input signal could possibly go as low as -1 V. Because the amplifier is powered from a single supply, V_{EE} is ground, so the necessary series resistance should be 2 k Ω .

Input Offset Voltage

The OPx81 family of op amps was designed for low offset voltages less than 1 mV.

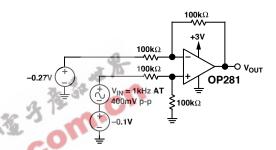


Figure 2. Single OPx81 Channel Configured as a Difference Amplifier Operating at $V_{CM} < 0 V$

Input Common-Mode Voltage Range

The OPx81 is rated with an input common-mode voltage range from V_{EE} to 1 V under V_{CC} . However, the op amp can still operate even with a common-mode voltage that is slightly *less* than V_{EE} . Figure 2 shows a single OPx81 channel configured as a difference amplifier with a single-supply voltage of 3 V. Negative dc voltages are applied at both input terminals creating a common-mode voltage that is less than ground. A 400 mV p-p input signal is then applied to the noninverting input. Figure 3 shows the input and output waves. Notice how the output of the amplifier also drops slightly *negative* without distortion.

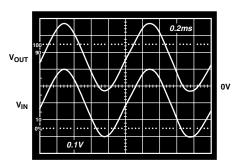


Figure 3. Input and Output Signals with $V_{CM} < 0 V$

Capacitive Loading

Most low supply current amplifiers have difficulty driving capacitive loads due to the higher currents required from the output stage for such loads. Higher capacitance at the output will increase the amount of overshoot and ringing in the amplifier's step response and could even affect the stability of the device. However, through careful design of the output stage and its high phase margin, the OPx81 family can tolerate some degree of capacitive loading. Figure 4 shows the step response of a single channel with a 10 nF capacitor connected at the output. Notice that the overshoot of the output does not exceed more than 10% with such a load, even with a supply voltage of only 3 V.

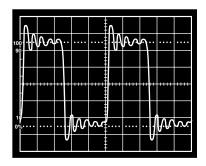


Figure 4. Ringing and Overshoot of the Output of the Amplifier

Micropower Reference Voltage Generator

Many single-supply circuits are configured with the circuit biased to 1/2 of the supply voltage. In these cases, a false ground reference can be created by using a voltage divider buffered by an amplifier. Figure 5 shows the schematic for such a circuit.

The two 1 M Ω resistors generate the reference voltage while drawing only 1.5 μ A of current from a 3 V supply. A capacitor connected from the inverting terminal to the output of the op amp provides compensation to allow for a bypass capacitor to be connected at the reference output. This bypass capacitor helps to establish an ac ground for the reference output. The entire reference generator draws less than 5 μ A from a 3 V supply source.

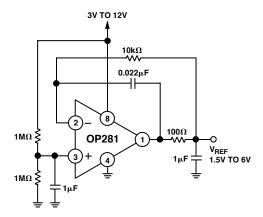


Figure 5. Single Channel Configured as a Micropower Bias Voltage Generator

Window Comparator

The extremely low power supply current demands of the OPx81 family make it ideal for use in long-life battery-powered applications such as a monitoring system. Figure 6 shows a circuit that uses the OP281 as a window comparator.

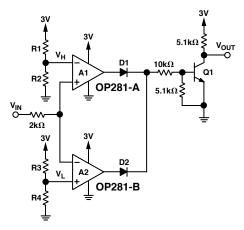


Figure 6. Using the OP281 as a Window Comparator

The threshold limits for the window are set by V_H and V_L, provided that $V_H > V_L$. The output of A1 will stay at the negative rail, in this case ground, as long as the input voltage is less than $V_{\rm H}$. Similarly, the output of A2 will stay at ground as long the input voltage is higher than V_L . As long as V_{IN} remains between V_L and V_H , the outputs of both op amps will be 0 V. With no current flowing in either D1 or D2, the base of Q1 will stay at ground, putting the transistor in cutoff and forcing V_{OUT} to the positive supply rail. If the input voltage rises above $V_{\rm H}$, the output of A2 stays at ground, but the output of A1 will go to the positive rail, and D1 will conduct current. This creates a base voltage that will turn on Q1 and drive VOUT low. The same condition occurs if V_{IN} falls below V_L with A2's output going high, and D2 conducting current. Therefore, V_{OUT} will be high if the input voltage is between V_L and V_H, and V_{OUT} will be low if the input voltage moves outside of that range.

The R1 and R2 voltage divider sets the upper window voltage, and the R3 and R4 voltage divider sets the lower voltage for the window. For the window comparator to function properly, V_H must be a greater voltage than V_L .

$$V_H = \frac{R2}{R1 + R2}$$
$$V_L = \frac{R4}{R3 + R4}$$

The 2 k Ω resistor connects the input voltage to the input terminals to the op amps. This protects the OP281 from possible excess current flowing into the input stages of the devices. D1 and D2 are small-signal switching diodes (1N4446 or equivalent), and Q1 is a 2N2222 or equivalent NPN transistor.

Low-Side Current Monitor

In the design of power supply control circuits, a great deal of design effort is focused on ensuring a pass transistor's long-term reliability over a wide range of load current conditions. As a result, monitoring and limiting device power dissipation is of prime importance in these designs. Figure 7 shows an example of a 5 V, single-supply current monitor that can be incorporated into the design of a voltage regulator with fold-back current limiting or a high current power supply with crowbar protection. The design capitalizes on the OPx81's common-mode range that extends to ground. Current is monitored in the power supply return path where a 0.1 Ω shunt resistor, R_{SENSE}, creates a very small voltage drop. The voltage at the inverting terminal becomes equal to the voltage at the noninverting terminal through the feedback of Q1, which is a 2N2222 or equivalent NPN transistor. This makes the voltage drop across R1 equal to the voltage drop across R_{SENSE}. Therefore, the current through Q1 becomes directly proportional to the current through R_{SENSE}, and the output voltage is given by:

$$V_{OUT} = V_{EE} - \left(\frac{R2}{R1} \times R_{SENSE} \times I_L\right)$$

The voltage drop across R2 increases with I_L increasing, so V_{OUT} decreases with higher supply current being sensed. For the element values shown, the V_{OUT} transfer characteristic is –2.5 V/A, decreasing from V_{EE} .

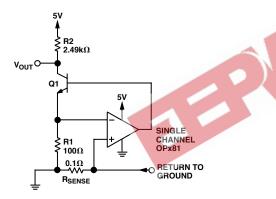


Figure 7. Low-Side Load Current Monitor

Low Voltage Half-Wave and Full-Wave Rectifiers Because of its quick overdrive recovery time, an OP281 can be configured as a full-wave rectifier for low frequency (<500 Hz) applications. Figure 8 shows the schematic.

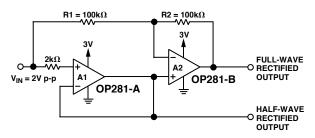


Figure 8. Single-Supply Full-Wave and Half-Wave Rectifiers Using an OP281

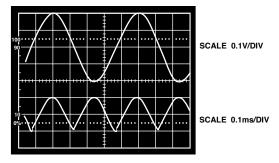


Figure 9. Full-Wave Rectified Signal

Amplifier A1 is used as a voltage follower that will track the input voltage only when it is greater than 0 V. This provides a half-wave rectification of the input signal to the noninverting terminal of amplifier A2. When A1's output is following the input, the inverting terminal of A2 will also follow the input from the virtual ground between the inverting and noninverting terminals of A2. With no potential difference across R1, no current flows through either R1 or R2, therefore the output of A2 will also follow the input. Now, when the input voltage goes below 0 V, the noninverting terminal of A2 becomes 0 V. This makes A2 work as an inverting amplifier with a gain of 1 and provides a full-wave rectified version of the input signal. A 2 k Ω resistor in series with A1's noninverting input protects the device when the input signal becomes less than ground.

Battery-Powered Telephone Headset Amplifier

Figure 10 shows how the OP281 can be used as a two-way amplifier in a telephone headset. One side of the OP281 can be used as an amplifier for the microphone, while the other side can be used to drive the speaker. A typical telephone headset uses a 600Ω speaker and an electret microphone that requires a supply voltage and a biasing resistor.

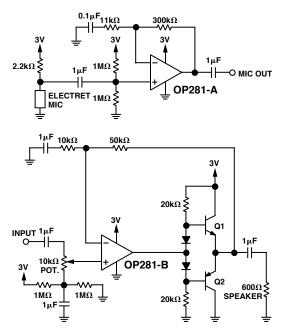


Figure 10. Two-Way Amplifier in a Battery-Powered Telephone Headset

The OP281-A op amp provides about 29 dB of gain for audio signals coming from the microphone. The gain is set by the 300 k Ω and 11 k Ω resistors. The gain bandwidth product of the amplifier is 95 kHz, which, for the set gain of 28, yields a –3 dB rolloff at 3.4 kHz. This is acceptable since telephone audio is band limited for 300 kHz to 3 kHz signals. If higher gain is required for the microphone, an additional gain stage should be used, as adding any more gain to the OP281 would limit the audio bandwidth. A 2.2 k Ω resistor is used to bias the electret microphone. This resistor value may vary depending on the specifications on the microphone being used. The output of the microphone is accoupled to the noninverting terminal of the op amp. Two 1 M Ω resistors are used to provide the dc offset for single-supply use.

The OP281-B amplifier can provide up to 15 dB of gain for the headset speaker. Incoming audio signals are ac-coupled to a 10 k Ω potentiometer that is used to adjust the volume. Again, two 1 M Ω resistors provide the dc offset with a 1 μ F capacitor establishing an ac ground for the volume control potentiometer. Because the OP281 is a rail-to-rail output amplifier, it would have difficulty driving a 600 Ω speaker directly. Here, a class AB buffer is used to isolate the load from the amplifier and also provide the necessary current drive to the speaker. By placing the buffer in the feedback loop of the op amp, crossover distortion can be minimized. Q1 and Q2 should have minimum betas of 100. The 600Ω speaker is ac-coupled to the emitters to prevent any quiescent current from flowing in the speaker. The 1 µF coupling capacitor makes an equivalent high-pass filter cutoff at 265 Hz with a 600 Ω load attached. Again, this does not pose a problem, as it is outside the frequency range for telephone audio signals.

The circuit in Figure 10 draws around $250 \,\mu$ A of current. The class AB buffer has a quiescent current of 140 μ A while roughly 100 μ A is drawn by the microphone itself. A CR2032 3 V lithium battery has a life expectancy of 160 mA hours, which means this circuit could run continuously for 640 hours on a single battery.

SPICE Macro-Model

Single OPx81 Channel SPICE Macro-model

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* 9/96, Ver. 1
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- * Copyright 1996 by Analog Devices
- *
- * Refer to "README.DOC" file for License Statement. Use of this
- * model indicates your acceptance of the terms and provisions in the
- * License Statement.
- *
- * Node Assignments

		0									
*				nonir	noninverting input						
*					inverting input						
*				i	positive supply						
*				i	i	Î		ative suppl	lv		
*				i i	i	ĺ		output	5		
*				i	Ì	ĺ	i				
*					ł						
.SUE	BCKT	OPx	81	1	2	99	50	45			
*											
* IN	PUT S	TAC	θE								
*											
Q1	4	1	3	PIX							
Q2	6	7	5	PIX							
I1	99	8	1.2	8E-6							

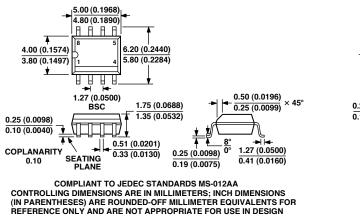
RC2 RE1 RE2 V1 9 V2 9 D1 D2 *	7 2 1 2 4 50 6 50 3 8 5 8 9 13 9 14 3 13 5 14	1E-10 500E3 500E3 108 108 DC .9 DC .9 DX DX	(12, 98) 80E-6 1	
* CMRI *	R76dB,	ZERO AT	1kHz	
ECM1 R1 C1	11 98 11 12 11 12 12 98	POLY(2) 1.59E6 100E-12 283	(1, 98) (2, 98) 0 .5 .5	
* POLE AT 900kHz				
R3 C2 * * POLE	98 0 98 20 20 98 20 98 20 98	(90, 0) (4, 6) 1E6 177E-15 kHz	1 1E-6	
* E2 R4 C3 *	21 98 21 22 22 98	(20, 98) 1E6 320E-15	1	
	STAGE			
* CF 4 R5 4 G3 9 D3 4 D4 4 V3 9 V4 4 *	45 40 40 98 98 40 40 41 42 40 99 41 42 50	8. 5E-12 65. 65E6 (22, 98) DX DX DC 0.5 DC 0.5	4.08E-7	
	PUT STA	GE		
EG1 9 EG2 4 * * MOD *	9990 9050 9546 9547 9946 9750 ELS	50 50 POLY(1) POLY(1)	POX L=1.5u W=300u NOX L=1.5u W=300u (98, 40) 0.77 1 (40, 98) 0.77 1	
LAMBI .MODE LAMBI .MODE	DA=0.01) EL NOX DA=0.01) EL PIX	NMOS (L		

OUTLINE DIMENSIONS

8-Lead Standard Small Outline Package [SOIC]

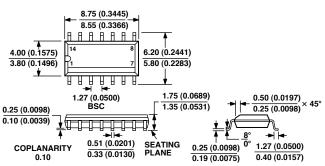
Narrow Body (R-8)

Dimensions shown in millimeters and (inches)



14-Lead Standard Small Outline Package [SOIC] Narrow Body (R-14)

Dimensions shown in millimeters and (inches)



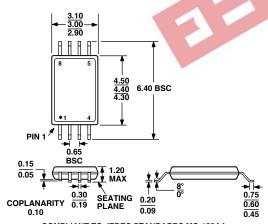
COMPLIANT TO JEDEC STANDARDS MS-012AB CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN

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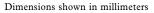
8-Lead Thin Shrink Small Outline Package [TSSOP] (RU-8)

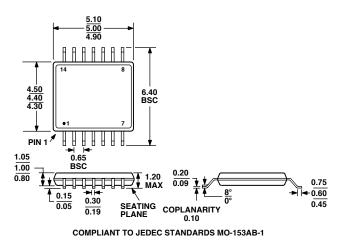
Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-153AA

14-Lead Thin Shrink Small Outline Package [TSSOP] (RU-14)





Revision History

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03—Data Sheet changed from REV. A to REV. B.	
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03—Data Sheet changed from REV. 0 to REV. A.	
Ipdated format	ıl
Peleted OP181Universa	ıl
Pdated package options	ıl
Peleted OP181 PIN CONFIGURATIONS	1
Peleted Epoxy DIP PIN CONFIGURATIONS	1
Thanges to ABSOLUTE MAXIMUM RATINGS	5
hanges to ORDERING GUIDE	5
hanges to Input Offset Voltage	0
Deleted former Figure 33 1	0
Peleted Overdrive Recovery Time section	1
Deleted former Figure 36 1	
eleted 8-Lead and 14-Lead Plastic DIP (N-8 and N-14) OUTLINE DIMENSIONS	4
pdated OUTLINE DIMENSIONS	4

CONTRACTOR

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